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Kind regards,

Team Nexperia

PNP/PNP resistor-equipped transistors;

R1 = 47 kΩ, R2 = 47 kΩ

Rev. 3 — 17 November 2011

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1.	Product	overview

Type number	Package			······································	
	NXP	JEITA	complement	complement	configuration
PEMB2	SOT666	-	PEMD12	PEMH2	ultra small and flat lead
PUMB2	SOT363	SC-88	PUMD12	PUMH2	very small

Reduces component count

AEC-Q101 qualified

Reduces pick and place costs

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _O	output current		-	-	-100	mA
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



1

| | 2 3 006aaa212

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline Graphic symbol	
1	GND (emitter) TR1		
2	input (base) TR1		_
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		²
6	output (collector) TR1		

3. Ordering information

Table 4. Ord	Table 4. Ordering information				
Type number Package					
	Name	Description	Version		
PEMB2	-	plastic surface-mounted package; 6 leads	SOT666		
PUMB2	SC-88	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

Marking code ^[1]
B2
B*2

[1] * = placeholder for manufacturing site code

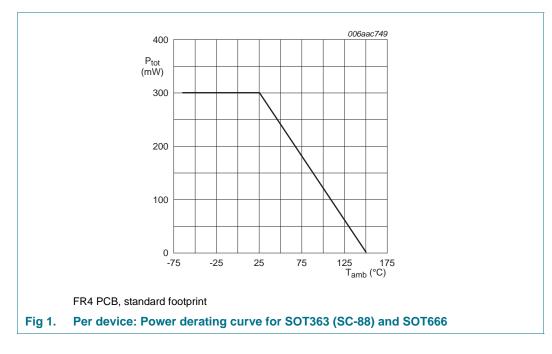
5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base	-	-50	V
V _{EBO}	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		-	+10	V
	negative		-	-40	V
lo	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \leq 25 ~^{\circ}C$			
	PEMB2 (SOT666)		[1][2] _	200	mW
	PUMB2 (SOT363)		<u>[1]</u> -	200	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	PEMB2 (SOT666)		[1][2] _	300	mW
	PUMB2 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



6. Thermal characteristics

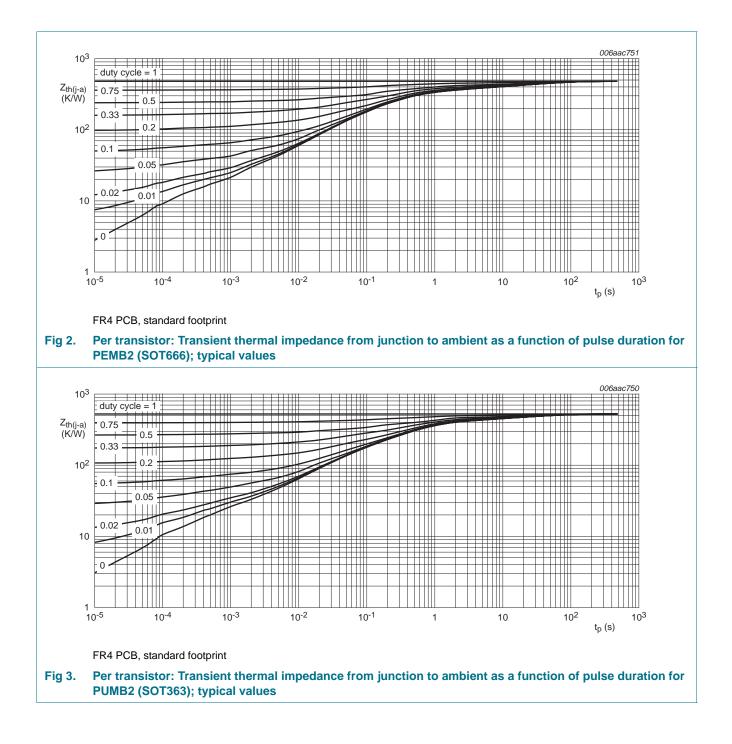
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMB2 (SOT666)		<u>[1][2]</u> _	-	625	K/W
	PUMB2 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device	9					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air				
	PEMB2 (SOT666)		<u>[1][2]</u> _	-	417	K/W
	PUMB2 (SOT363)		<u>[1]</u> _	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

PEMB2; PUMB2

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



7. Characteristics

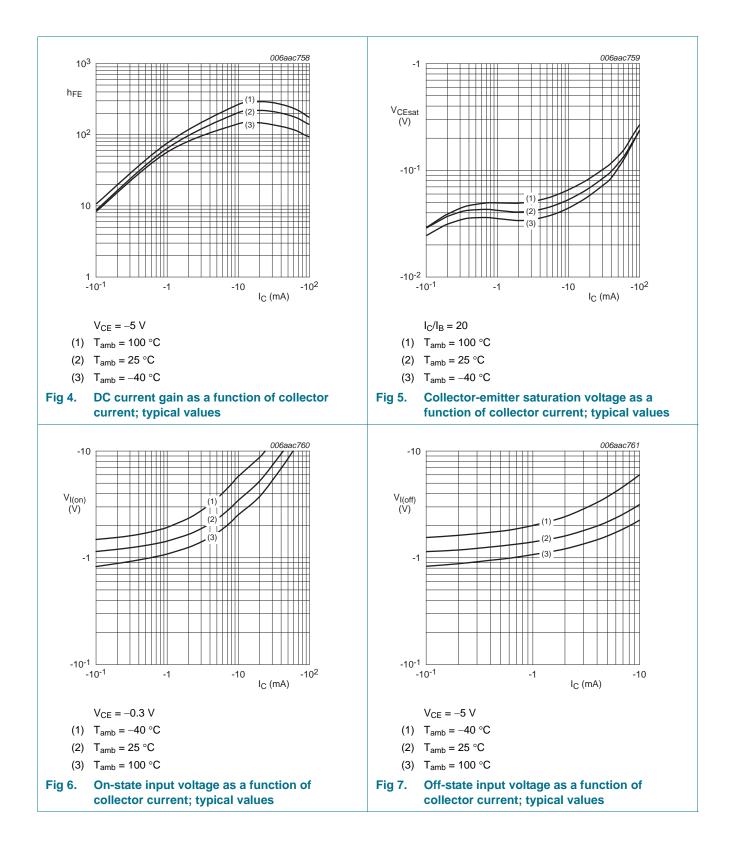
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = -30$ V; $I_B = 0$ A	-	-	-1	μA
	current	$\label{eq:VCE} \begin{array}{l} V_{CE} = -30 \ V; \ I_{B} = 0 \ A; \\ T_{j} = 150 \ ^{\circ}C \end{array}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-90	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -5 \text{ mA}$	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA}; I_{B} = -0.5 \text{ mA}$	-	-	-150	mV
V _{I(off)}	off-state input voltage	V_{CE} = -5 V; I_{C} = $-100~\mu A$	-	-1.2	-0.8	V
V _{I(on)}	on-state input voltage	V_{CE} = -0.3 V; I_{C} = -2 mA	-3	-1.6	-	V
R1	bias resistor 1 (input)		33	47	61	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -10 \text{ mA}; \text{ I}_{C} = 100 \text{ MHz}$	1] _	180	-	MHz

[1] Characteristics of built-in transistor

PEMB2_PUMB2 Product data sheet

PEMB2; PUMB2

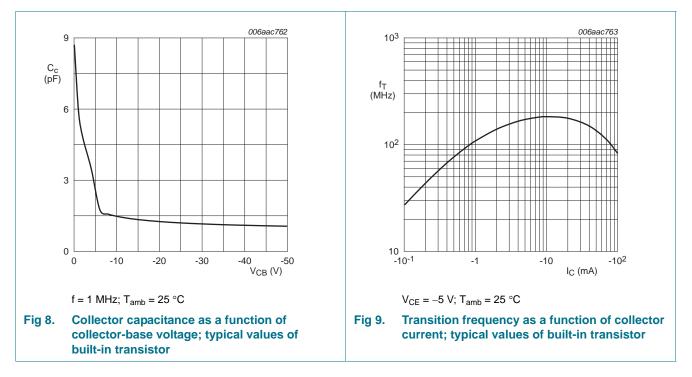
PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



PEMB2 PUMB2

PEMB2; PUMB2

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

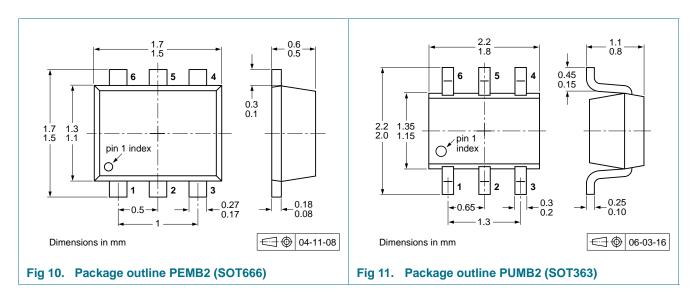


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

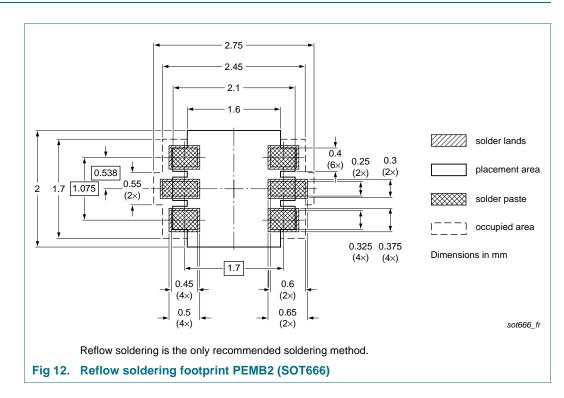
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

•••		Description		Packing quantity			
number				3000	4000	8000	10000
PEMB2	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
PUMB2	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

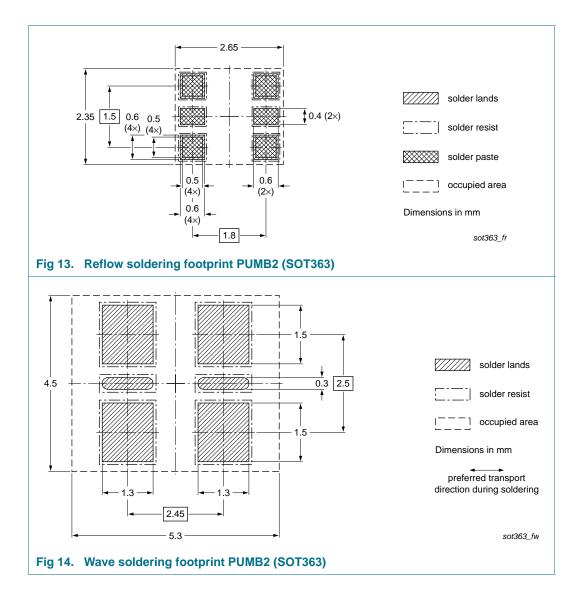
[1] For further information and the availability of packing methods, see Section 14.

- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering



PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω



PEMB2_PUMB2 Product data sheet

12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMB2_PUMB2 v.3	20111117	Product data sheet	-	PEMB2_PUMB2 v.2		
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 					
	 Legal texts have been adapted to the new company name where appropriate. 					
	Section 1 "I	Product profile": updated				
	 <u>Section 4 "Marking</u>": updated 					
	• Figure 1 to 9: added					
	 <u>Section 5 "Limiting values"</u>: updated 					
	 <u>Section 6 "Thermal characteristics"</u>: updated 					
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined 					
	to $V_{I(off)}$ off-state input voltage, I_{CEO} updated, f_T added					
	Section 8 "Test information": added					
	 <u>Section 9 "Package outline"</u>: superseded by minimized package outline drawing 					
	<u>Section 10 "Packing information"</u> : added					
	Section 11 "Soldering": added					
	Section 13	"Legal information": updated	l			
PEMB2_PUMB2 v.2	20031015	Product data sheet	-	PUMB2 v.1 PEMB2 v.1		
PEMB2 v.1	20010914	Product specification	-	-		
PUMB2 v.1	19910803	Product specification	-	-		

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PEMB2_PUMB2 Product data sheet

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

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PEMB2; PUMB2

PNP/PNP resistor-equipped transistors; R1 = 47 k Ω , R2 = 47 k Ω

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Date of release: 17 November 2011 Document identifier: PEMB2_PUMB2

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